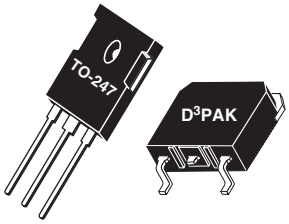
Microsemi
POWER PRODUCTS GROUP

APT38N60BC6
APT38N60SC6

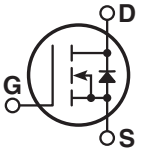
600V 38A 0.099Ω

COOLMOS
Power Semiconductors

Super Junction MOSFET



- **Ultra Low $R_{DS(ON)}$**
- **Low Miller Capacitance**
- **Ultra Low Gate Charge, Q_g**
- **Avalanche Energy Rated**
- **Extreme dv/dt Rated**
- **Popular TO-247 or Surface Mount D^3 package.**



MAXIMUM RATINGS

All Ratings per die: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT38N60B_SC6	UNIT
V_{DSS}	Drain-Source Voltage	600	Volts
I_D	Continuous Drain Current @ T_C = 25°C	38	Amps
	Continuous Drain Current @ T_C = 100°C	24	
I_{DM}	Pulsed Drain Current [1]	112	
V_{GS}	Gate-Source Voltage Continuous	±20	Volts
P_D	Total Power Dissipation @ T_C = 25°C	278	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	260	
dv/dt	Drain-Source Voltage slope (V_{DS} = 480V, I_D = 38A, T_J = 125°C)	15	V/ns
I_{AR}	Avalanche Current [2]	6.6	Amps
E_{AR}	Repetitive Avalanche Energy [2] (Id = 6.6A, Vdd = 50V)	1.2	mJ
E_{AS}	Single Pulse Avalanche Energy (Id = 6.6A, Vdd = 50V)	796	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{(DSS)}$	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250µA)	600			Volts
$R_{DS(on)}$	Drain-Source On-State Resistance [3] (V_{GS} = 10V, I_D = 18A)			0.099	Ohms
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = 600V, V_{GS} = 0V)			25	µA
	Zero Gate Voltage Drain Current (V_{DS} = 600V, V_{GS} = 0V, T_C = 150°C)			100	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±20V, V_{DS} = 0V)			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1.2mA)	2.5	3	3.5	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		2826		pF
C_{oss}	Output Capacitance			2428		
C_{rss}	Reverse Transfer Capacitance			261		
Q_g	Total Gate Charge [4]	V_{GS} = 10V V_{DD} = 300V I_D = 38A @ 25°C		112		nC
Q_{gs}	Gate-Source Charge			18		
Q_{gd}	Gate-Drain ("Miller") Charge			58		
$t_{d(on)}$	Turn-on Delay Time	**INDUCTIVE SWITCHING** V_{GS} = 15V V_{DD} = 400V I_D = 38A @ 25°C R_G = 4.3Ω		14		ns
t_r	Rise Time			29		
$t_{d(off)}$	Turn-off Delay Time			118		
t_f	Fall Time			69		
E_{on}	Turn-on Switching Energy [5]	**INDUCTIVE SWITCHING @ 25°C** V_{DD} = 400V, V_{GS} = 15V I_D = 38A, R_G = 4.3Ω		710		µJ
E_{off}	Turn-off Switching Energy			550		
E_{on}	Turn-on Switching Energy [5]	**INDUCTIVE SWITCHING @ 125°C** V_{DD} = 400V, V_{GS} = 15V I_D = 38A, R_G = 4.3Ω		1100		
E_{off}	Turn-off Switching Energy			625		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)				33	Amps
I_{SM}	Pulsed Source Current [1] (Body Diode)				112	
V_{SD}	Diode Forward Voltage [3] (V_{GS} = 0V, I_S = -38A)				1.3	Volts
$^{dv}/_{dt}$	Peak Diode Recovery $^{dv}/_{dt}$ [6]				8	V/ns
t_{rr}	Reverse Recovery Time (I_S = -38A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		667		ns
Q_{rr}	Reverse Recovery Charge (I_S = -38A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		18		µC
I_{RRM}	Peak Recovery Current (I_S = -38A, $^{di}/_{dt}$ = 100A/µs)	T_j = 25°C		49		Amps

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.45	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

1 Repetitive Rating: Pulse width limited by maximum junction temperature

2 Repetitive avalanche causes additional power losses that can be calculated as ***$P_{AV} = E_{AR}*f$. Pulse width tp limited by Tj max.***

3 Pulse Test: Pulse width < 380 µs, Duty Cycle < 2%

4 See MIL-STD-750 Method 3471

5 Eon includes diode reverse recovery.

6 Maximum 125°C diode commutation speed = di/dt 600A/µs

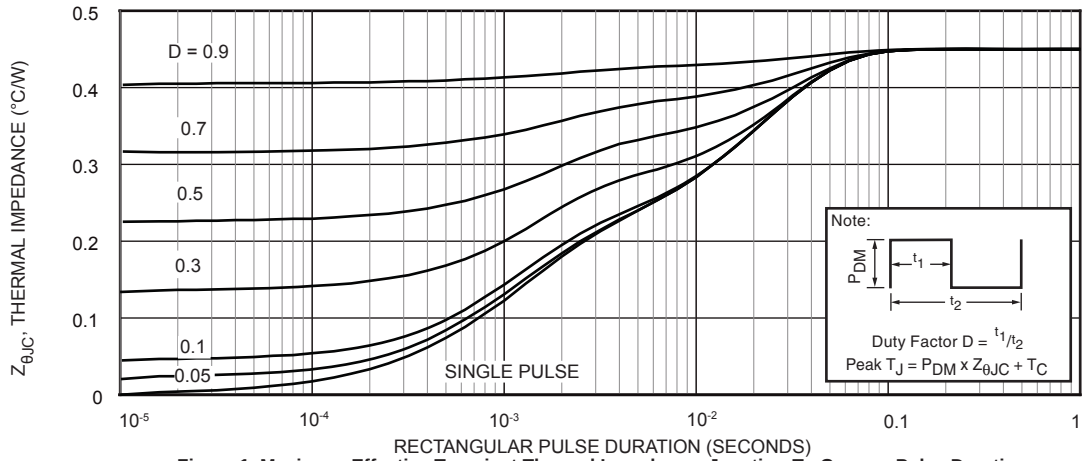


Figure 1, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

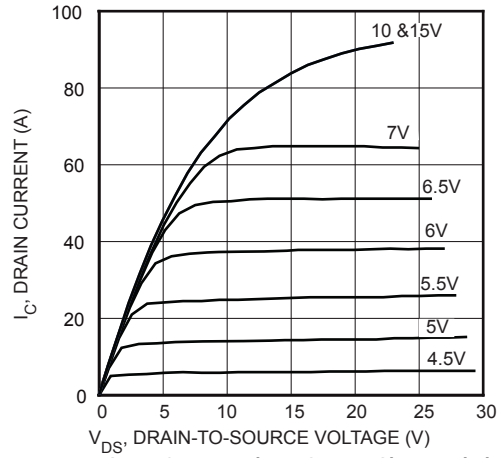


FIGURE 2, Low Voltage Output Characteristics

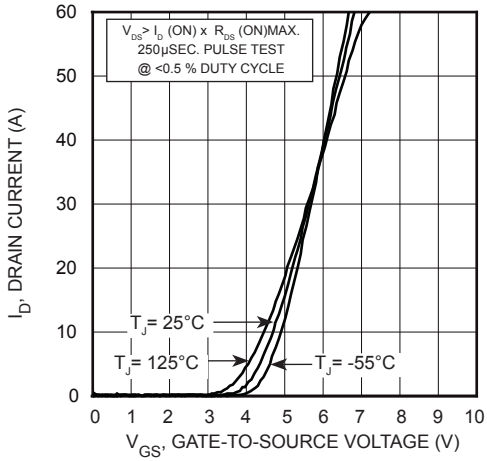


FIGURE 3, Transfer Characteristics

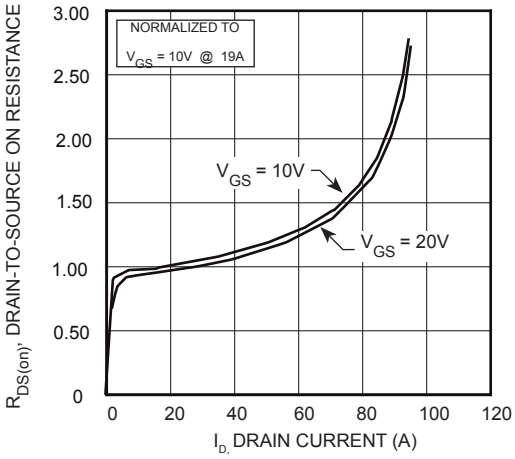


FIGURE 4, R_{DS}(ON) vs Drain Current

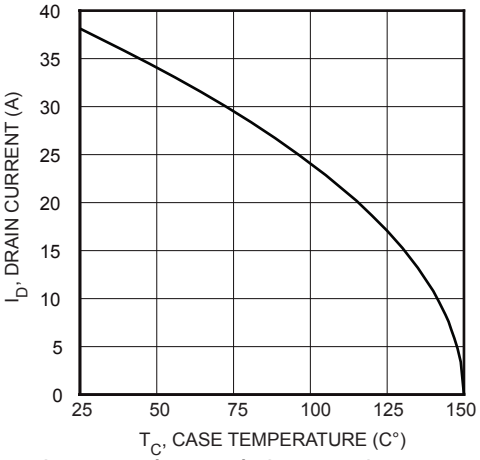


FIGURE 5, Maximum Drain Current vs Case Temperature

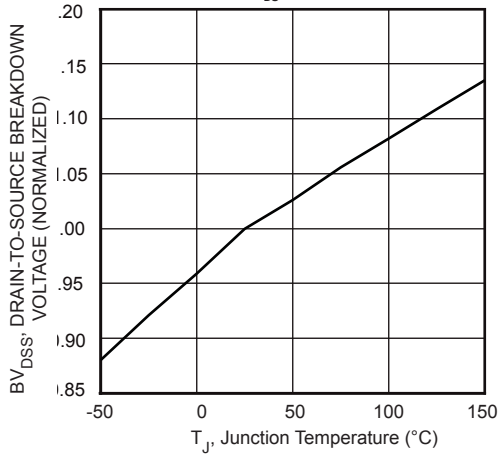


FIGURE 6, Breakdown Voltage vs Temperature

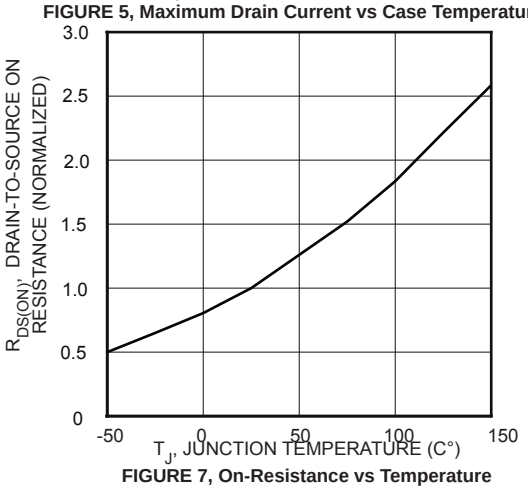


FIGURE 7, On-Resistance vs Temperature

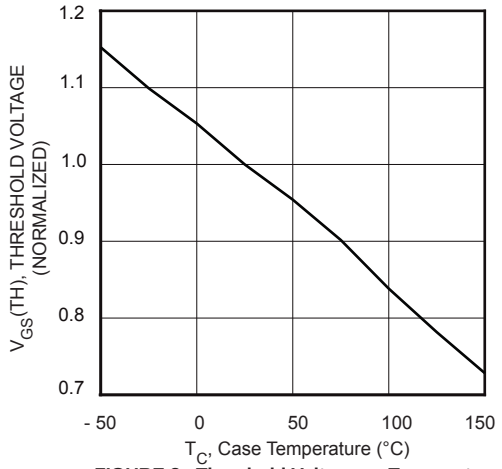


FIGURE 8, Threshold Voltage vs Temperature

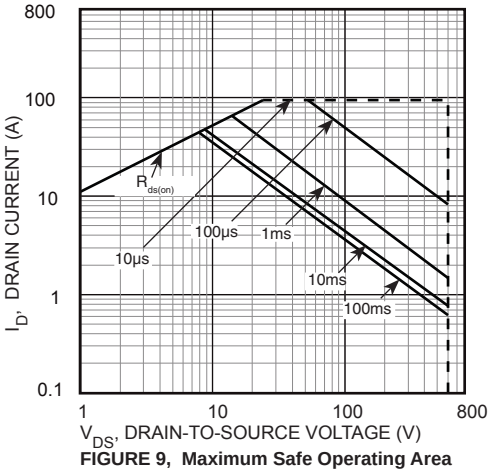


FIGURE 9, Maximum Safe Operating Area

Typical Performance Curves

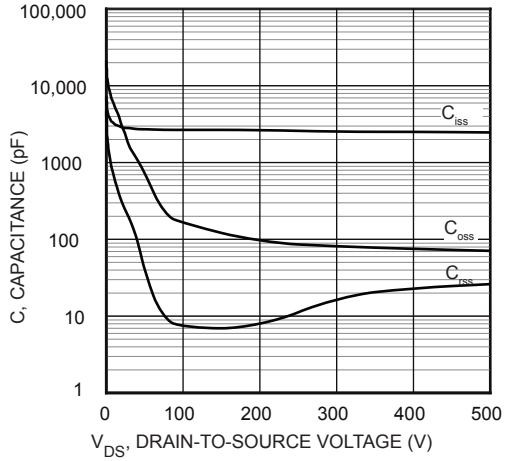


FIGURE 10, Capacitance vs Drain-To-Source Voltage

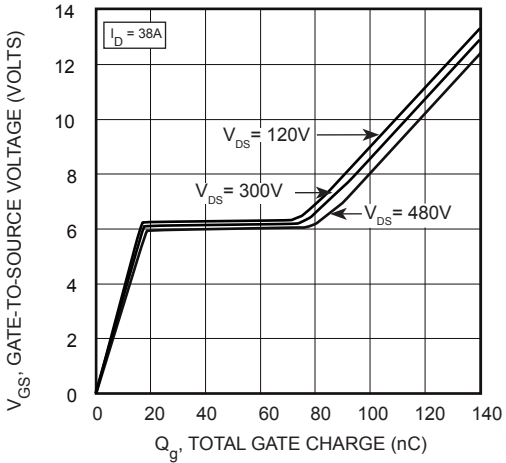


FIGURE 11, Gate Charges vs Gate-To-Source Voltage

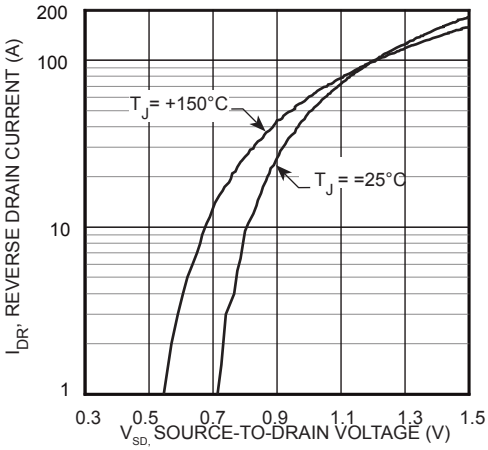


FIGURE 12, Source-Drain Diode Forward Voltage

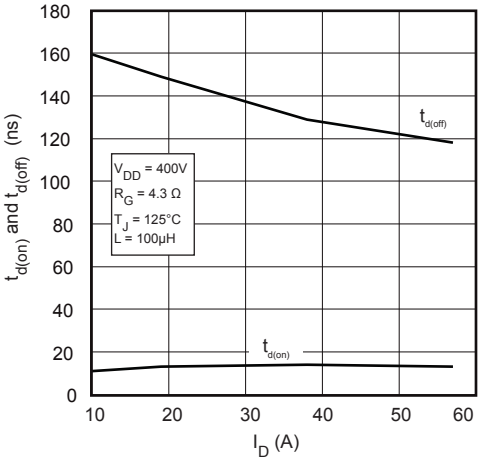


FIGURE 13, Delay Times vs Current

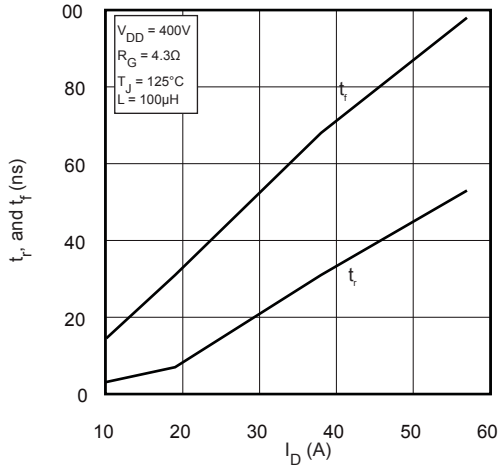


FIGURE 14 , Rise and Fall Times vs Current

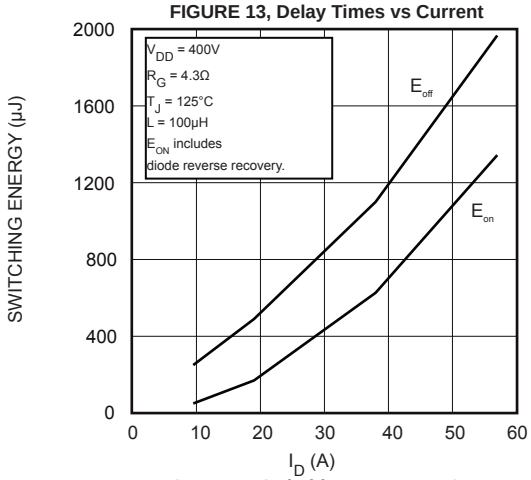


FIGURE 15, Switching Energy vs Current

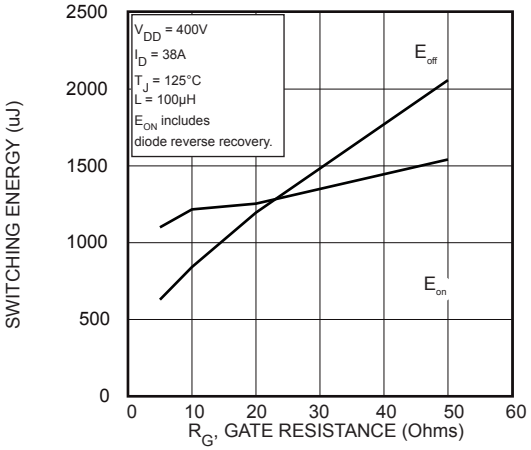


FIGURE 16, Switching Energy vs Gate Resistance

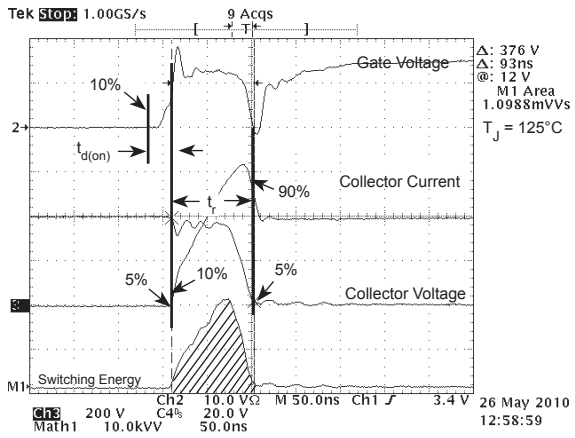


Figure 17, Turn-on Switching Waveforms and Definitions

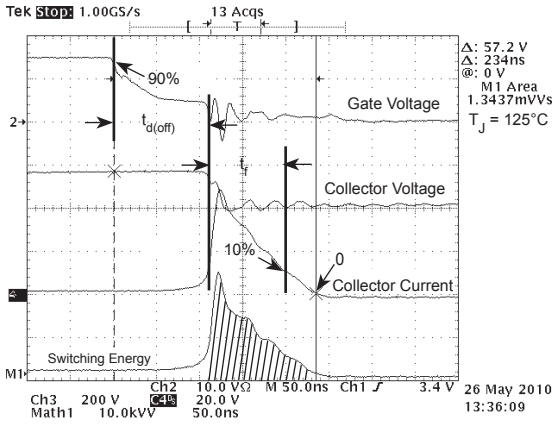


Figure 18, Turn-off Switching Waveforms and Definitions

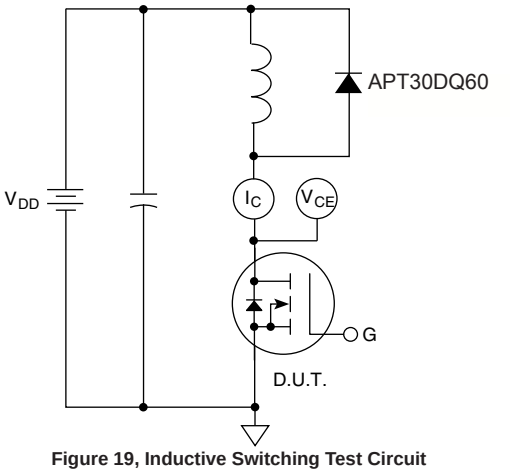
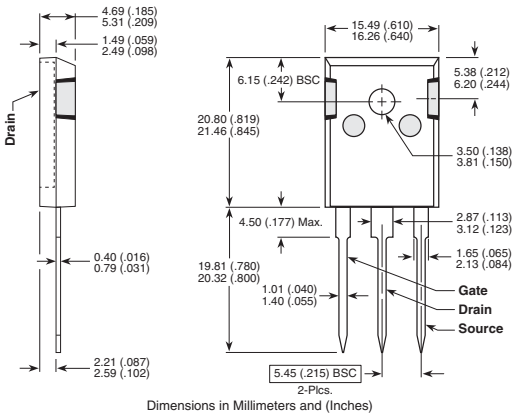


Figure 19, Inductive Switching Test Circuit

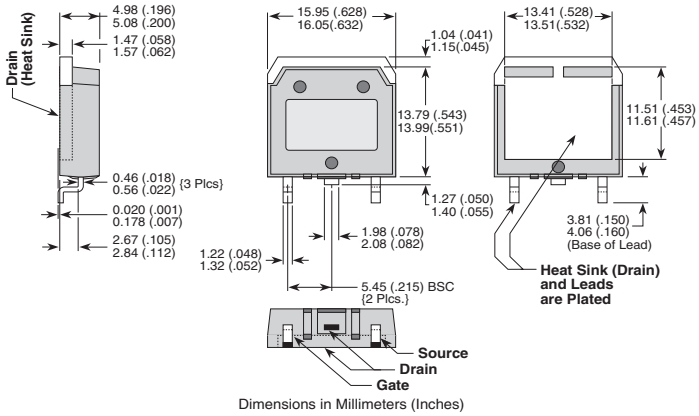
TO-247 (B) Package Outline



Dimensions in Millimeters and (Inches)

D^{3}PAK Package Outline

e3 100% Sn Plated



Dimensions in Millimeters (Inches)

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9